

MOS FIELD EFFECT TRANSISTOR μ PA2716GR

SWITCHING P-CHANNEL POWER MOS FET

DESCRIPTION

The µPA2716GR is P-Channel MOS Field Effect Transistor designed for power management applications of notebook computers and Li-ion battery protection circuit.

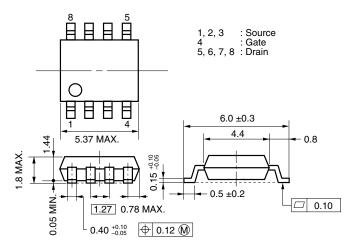
FEATURES

- · Low on-state resistance $R_{DS(on)1} = 7.0 \text{ m}\Omega \text{ MAX.} (V_{GS} = -10 \text{ V}, I_{D} = -7.0 \text{ A})$ $R_{DS(on)2} = 11.3 \text{ m}\Omega \text{ MAX.} (V_{GS} = -4.5 \text{ V}, I_{D} = -7.0 \text{ A})$
- Low Ciss: Ciss = 3000 pF TYP.
- · Built-in gate protection diode
- Small and surface mount package (Power SOP8)

ORDERING INFORMATION

PART NUMBER	PACKAGE
μPA2716GR	Power SOP8

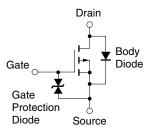
PACKAGE DRAWING (Unit: mm)



ABSOLUTE MAXIMUM RATINGS (TA = 25°C, All terminals are connected.)

	Drain to Source Voltage (V _{GS} = 0 V)	VDSS	-30	V
	Gate to Source Voltage (VDS = 0 V)	Vgss	∓20	V
	Drain Current (DC)	I _{D(DC)}	∓14	Α
	Drain Current (pulse) Note1	ID(pulse)	∓140	Α
	Total Power Dissipation Note2	P _{T1}	2	W
	Total Power Dissipation Note3	P _{T2}	2	W
	Channel Temperature	Tch	150	°C
	Storage Temperature	Tstg	-55 to + 150	°C
*	Single Avalanche Current Note4	las	-14	Α
	Single Avalanche Energy Note4	Eas	19.6	mJ

EQUIVALENT CIRCUIT



- **Notes 1.** PW \leq 10 μ s, Duty Cycle \leq 1%
 - 2. Mounted on ceramic substrate of 1200 mm² x 2.2 mm
 - 3. Mounted on glass epoxy board of 25.4 mm x 25.4 mm x 0.8 mm, PW = 10 sec
 - **4.** Starting T_{ch} = 25°C, V_{DD} = -15 V, R_G = 25 Ω , L = 100 μ H, V_{GS} = -20 \rightarrow 0 V

Remark The diode connected between the gate and source of the transistor serves as a protector against ESD. When this device actually used, an additional protection circuit is externally required if a voltage exceeding the rated voltage may be applied to this device.

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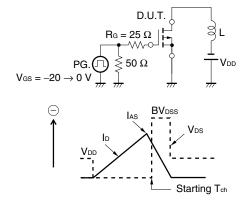


ELECTRICAL CHARACTERISTICS (TA = 25°C, All terminals are connected.)

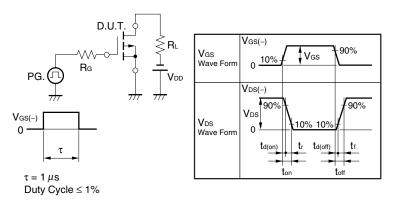
	CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
	Zero Gate Voltage Drain Current	Ipss	V _{DS} = -30 V, V _{GS} = 0 V			-1	μΑ
	Gate Leakage Current	Igss	$V_{GS} = \mp 20 \text{ V}, V_{DS} = 0 \text{ V}$			∓10	μΑ
	Gate Cut-off Voltage	V _{GS(off)}	V _{DS} = -10 V, I _D = -1 mA	-1.0		-2.5	V
	Forward Transfer Admittance Note	y fs	V _{DS} = -10 V, I _D = -7.0 A	10			S
	Drain to Source On-state Resistance Note	R _{DS(on)1}	$V_{GS} = -10 \text{ V}, I_D = -7.0 \text{ A}$		5.5	7.0	mΩ
		R _{DS(on)2}	$V_{GS} = -4.5 \text{ V}, I_D = -7.0 \text{ A}$		7.3	11.3	mΩ
*		R _{DS(on)3}	$V_{GS} = -4.0 \text{ V}, I_D = -7.0 \text{ A}$		8.3	13.5	mΩ
	Input Capacitance	Ciss	V _{DS} = -10 V		3000		pF
	Output Capacitance	Coss	V _{GS} = 0 V		960		pF
	Reverse Transfer Capacitance	Crss	f = 1 MHz		500		pF
	Turn-on Delay Time	t _{d(on)}	V _{DD} = -15 V, I _D = -7.0 A		14		ns
	Rise Time	t r	V _{GS} = -10 V		19		ns
	Turn-off Delay Time	$t_{\sf d(off)}$	R _G = 10 Ω		680		ns
	Fall Time	t f			340		ns
	Total Gate Charge	Q _G	V _{DD} = -24 V		95		nC
	Gate to Source Charge	Qgs	V _{GS} = -10 V		11		nC
	Gate to Drain Charge	Q _{GD}	I _D = -14 A		25		nC
	Body Diode Forward Voltage Note	V _{F(S-D)}	I _F = 14 A, V _{GS} = 0 V		0.83		V
	Reverse Recovery Time	trr	I _F = 14 A, V _{GS} = 0 V		380		ns
	Reverse Recovery Charge	Qrr	di/dt = 50 A/μs		690		nC

Note Pulsed

TEST CIRCUIT 1 AVALANCHE CAPABILITY



TEST CIRCUIT 2 SWITCHING TIME

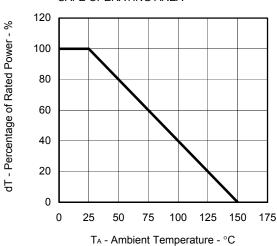


TEST CIRCUIT 3 GATE CHARGE

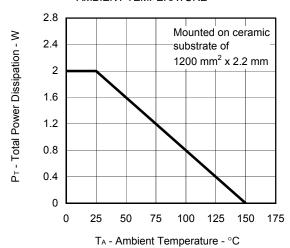
$$\begin{array}{c|c} D.U.T. & \\ \hline \\ I_G = -2 \text{ mA} \\ \hline \\ PG. & \\ \hline \end{array} \begin{array}{c} PG. & \\ \hline \\ \end{array} \begin{array}{c} PG. & \\ \hline \end{array} \begin{array}{c} \\ \\ \\ \\ \end{array} \begin{array}{c} \\ \\ \\ \\ \end{array} \begin{array}{c} \\ \\ \\ \\ \end{array} \begin{array}{c} \\ \\ \\ \\ \end{array} \begin{array}{c} \\ \\ \\ \end{array} \begin{array}{c} \\ \\ \\ \\ \\ \end{array} \begin{array}{c} \\ \\ \\ \\ \\ \end{array} \begin{array}{c} \\ \\ \\ \\ \\ \end{array} \begin{array}{c} \\ \\ \\ \\ \\ \end{array} \begin{array}{c} \\ \\ \\ \\ \end{array} \begin{array}{c} \\ \\ \\ \\ \\ \end{array} \begin{array}{c} \\ \\ \\ \\ \\ \end{array} \begin{array}{c} \\ \\ \\ \\$$

TYPICAL CHARACTERISTICS (TA = 25°C)

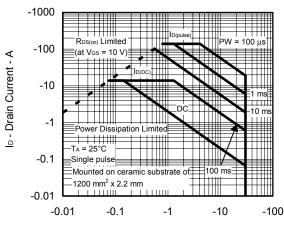
DERATING FACTOR OF FORWARD BIAS SAFE OPERATING AREA



TOTAL POWER DISSIPATION vs. AMBIENT TEMPERATURE

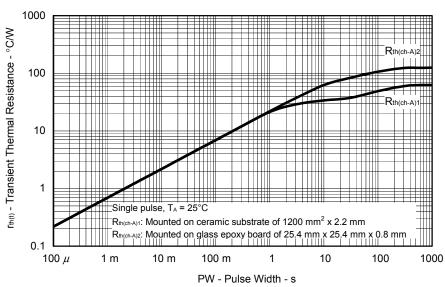


FORWARD BIAS SAFE OPERATING AREA



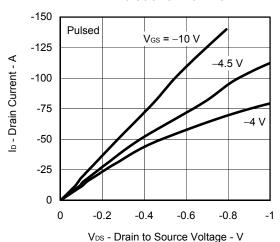
VDS - Drain to Source Voltage - V

TRANSIENT THERMAL RESISTANCE vs. PULSE WIDTH

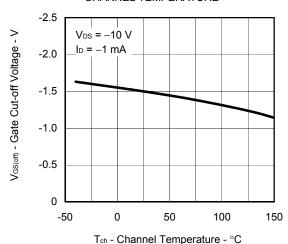


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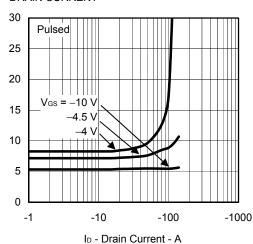
DRAIN CURRENT vs. DRAIN TO SOURCE VOLTAGE



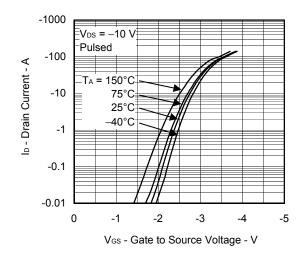
GATE CUT-OFF VOLTAGE vs. CHANNEL TEMPERATURE



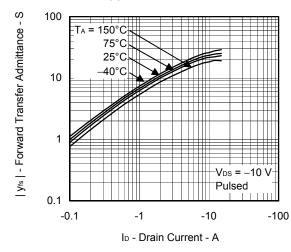
DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT



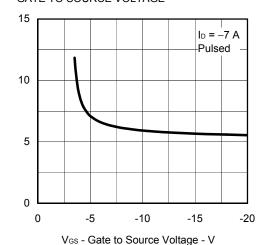
FORWARD TRANSFER CHARACTERISTICS



FORWARD TRANSFER ADMITTANCE vs. DRAIN CURRENT



DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE

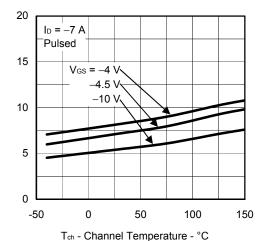


R_{DS(m)} - Drain to Source On-state Resistance - mΩ

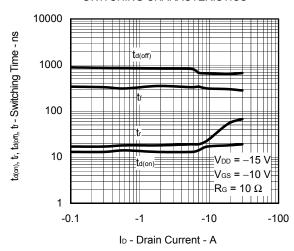
R_{DS(cn)} - Drain to Source On-state Resistance - mΩ

RDS(m) - Drain to Source On-state Resistance - m\Omega

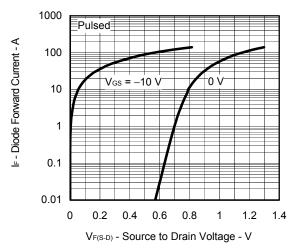
DRAIN TO SOURCE ON-STATE RESISTANCE vs. CHANNEL TEMPERATURE



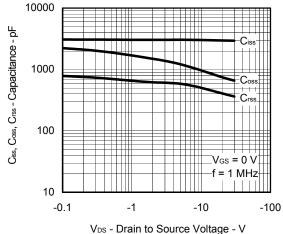
SWITCHING CHARACTERISTICS



SOURCE TO DRAIN DIODE FORWARD VOLTAGE

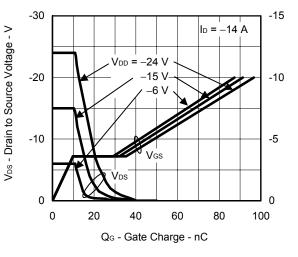


CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE

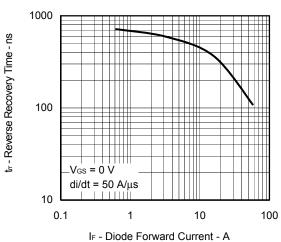


VDS - Dialit to Source Voltage - V

★ DYNAMIC INPUT/OUTPUT CHARACTERISTICS



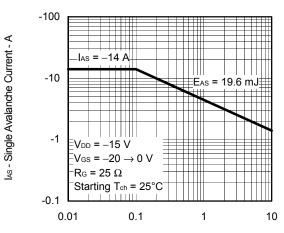
REVERSE RECOVERY TIME vs. DIODE FORWARD CURRENT



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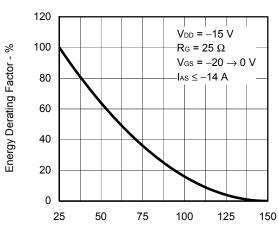
Vgs - Gate to Source Voltage - V

SINGLE AVALANCHE CURRENT vs. INDUCTIVE LOAD



L - Inductive Load - mH

SINGLE AVALANCHE ENERGY DERATING FACTOR



Starting T_{ch} - Starting Channel Temperature - $^{\circ}\text{C}$

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